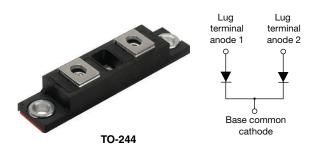


HEXFRED® Ultrafast Soft Recovery Diode, 280 A



PRODUCT SUMMARY					
I _{F(AV)}	280 A				
V_{R}	600 V				
I _{F(DC)} at T _C	149 A at 100 °C				
Package	TO-244 (TO-244AB)				
Circuit	Two diodes common cathode				

FEATURES

- Very low Q_{rr} and t_{rr}
- UL approved file E222165



 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



RoHS COMPLIAN

BENEFITS

- Reduced RFI and EMI
- · Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dI_F/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V_R		600	V
Continuous forward current		T _C = 25 °C	292	
Continuous forward current	I _F	T _C = 100 °C	149	Α
Single pulse forward current	I _{FSM}	Limited by junction temperature	600	
Non-repetitive avalanche energy	E _{AS}	$L = 100 \mu H$, duty cycle limited by maximum T_J	2.2	mJ
Maximum power dissipation P _D		T _C = 25 °C	657	W
Maximum power dissipation	P_{D}	T _C = 100 °C	263	VV
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
		I _F = 105 A		-	1.33	1.8	V
Maximum forward voltage	V_{FM}	I _F = 210 A	See fig. 1	-	1.53	2.1	
		I _F = 105 A, T _J = 125 °C		-	1.22	1.64	
Maximum reverse leakage current	I _{RM}	T _J = 125 °C, V _R = 600 V	See fig. 2	-	2.4	8	mA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	280	400	pF
Series inductance	L _S	From top of terminal hole to mounting plane		ı	5.0	-	nH



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	Payarsa racovary time		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		39	-	
See fig. 5	t _{rr}	T _J = 25 °C		-	92	140	ns
		T _J = 125 °C		-	180	270	
Peak recovery current	I _{RRM} -	T _J = 25 °C		-	9.3	17	А
See fig. 6		IRRM	T _J = 125 °C	I _F = 105 A dI _F /dt = 200 A/µs	-	16	30
Reverse recovery charge	Q _{rr}	T _J = 25 °C	$V_{R} = 200 \text{ V}$	-	490	1200	nC
See fig. 7		Q _{rr}	T _J = 125 °C		-	1400	4000
Peak rate of recovery current		dl _{(rec)M} /dt	T _J = 25 °C		-	290	-
See fig. 8			T _J = 125 °C		-	200	-

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}	-55	=	150	°C	
Thormal resistance, junction to case	per leg	- R _{thJC}	-	-	0.19	°C/W K/W	
Thermal resistance, junction to case	per module	PthJC	-	-	0.095		
Typical thermal resistance, case to heatsink		R _{thCS}	-	0.10	-		
Mainle			-	68	-	g	
Weight			-	2.4	-	oz.	
Mounting torque (1)			30 (3.4)	-	40 (4.6)		
Mounting torque (7)	center hole		12 (1.4)	-	18 (2.1)	lbf ⋅ in (N ⋅ m)	
Terminal torque			30 (3.4)	-	40 (4.6)	(** ***)	
Vertical pull			-	-	80	- lbf · in	
2" lever pull			-	-	35		

Note

⁽¹⁾ Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.

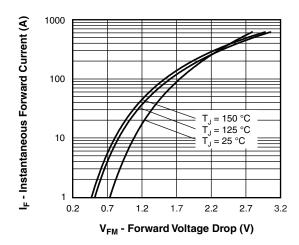


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

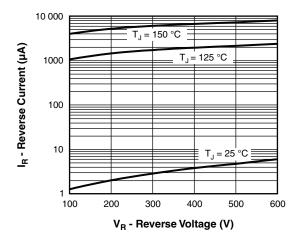


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

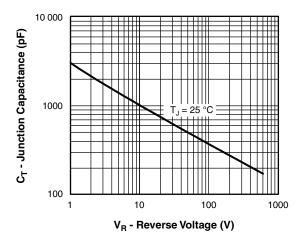


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

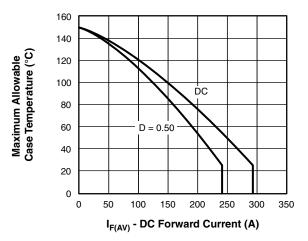


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

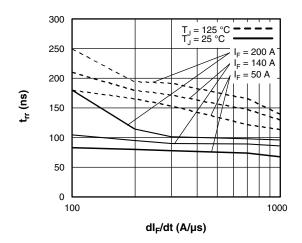


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

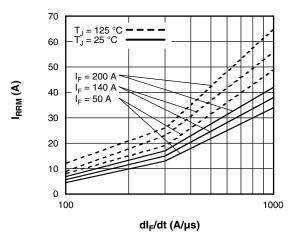


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

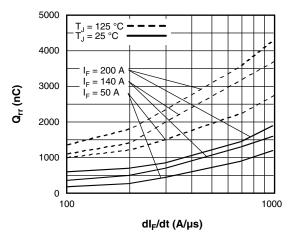


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

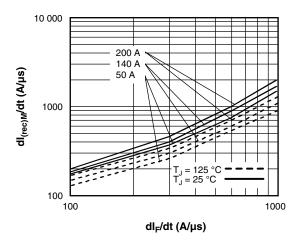


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

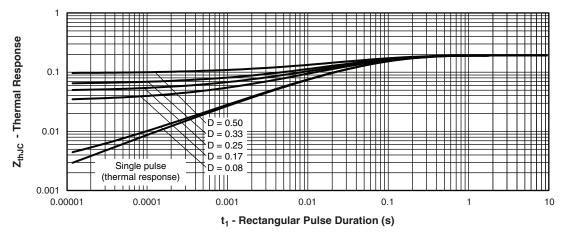


Fig. 9 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

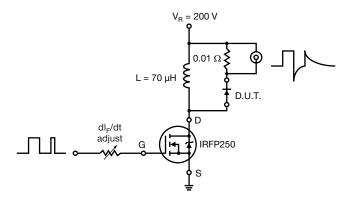
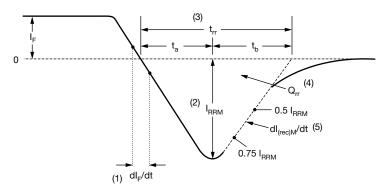


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) $\boldsymbol{I}_{\text{RRM}}$ peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_{b} portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions



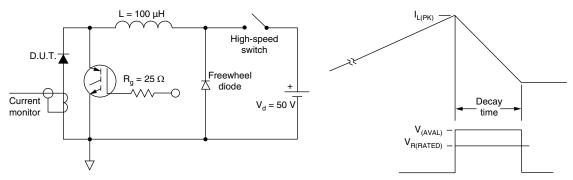
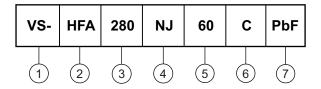


Fig. 12 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

Device code



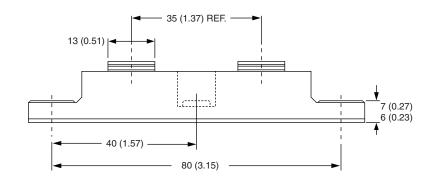
- 1 Vishay Semiconductors product
- 2 HEXFRED® family, electron irradiated
- 3 Average current rating
- **4** NJ = TO-224
- 5 Voltage rating (600 V)
- 6 C = Common cathode
- 7 Lead (Pb)-free

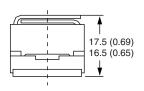
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95021			

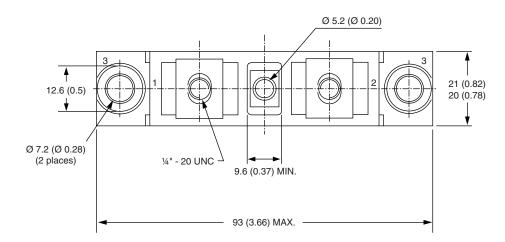


TO-244

DIMENSIONS in millimeters (inches)









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